

DESCRIPTION:

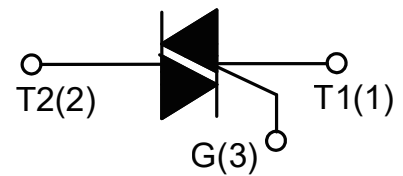
With high ability to withstand the shock loading of large current, BTA216-800B series triacs provide high dv/dt rate with strong resistance to electro-magnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.



TO-263

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	600/800/1200	V


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600/800/1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600/800/1200	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	$I_{T(RMS)}$	16	A
	TO-263 ($T_C=80^\circ\text{C}$)		
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)	I_{TSM}	160	A
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	128	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value				Unit
				BW	CW	SW	TW	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	50	35	10	5	mA
V_{GT}		I - II -III	MAX	1.3				V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	70	50	30	15	mA
		II		80	60	40	20	
I_H	$I_T=100\text{mA}$		MAX	60	40	25	15	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	1000	500	200	100	V/ μs

4 Quadrants

Symbol	Test Condition	Quadrant		Value		Unit
				B	C	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	50	25	mA
		IV		70	50	
V_{GT}		ALL	MAX	1.5		V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I -III-IV	MAX	70	50	mA
		II		100	80	
I_H	$I_T=100\text{mA}$		MAX	60	40	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	500	200	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)			Unit
			-600V	-800V	-1200V	
V_{TM}	$I_{TM}=22.5\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5			V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	5	10	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	1	2	mA

**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-263	2.5	°C/W
$R_{th(j-a)}$	junction to ambient		45	

FIG.1 Maximum power dissipation versus RMS on-state current

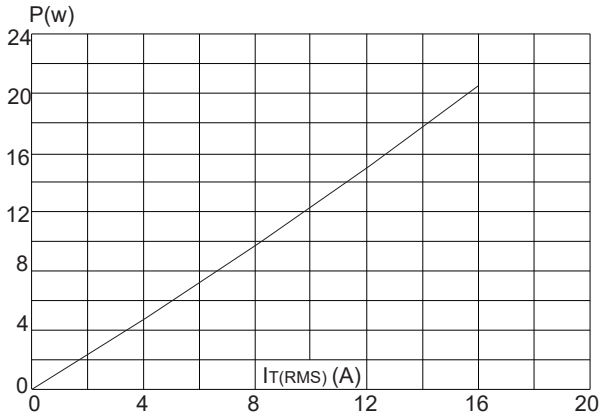


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35 μ m)(full cycle)

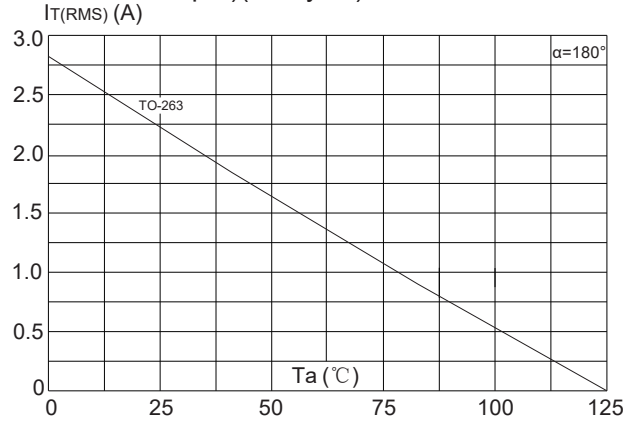


FIG.3: Surge peak on-state current versus number of cycles

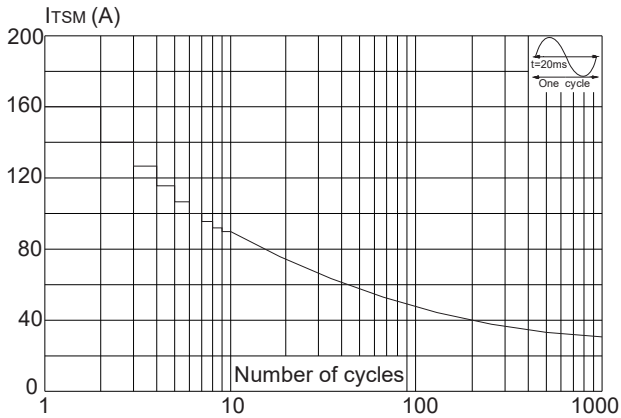


FIG.4: On-state characteristics (maximum values)

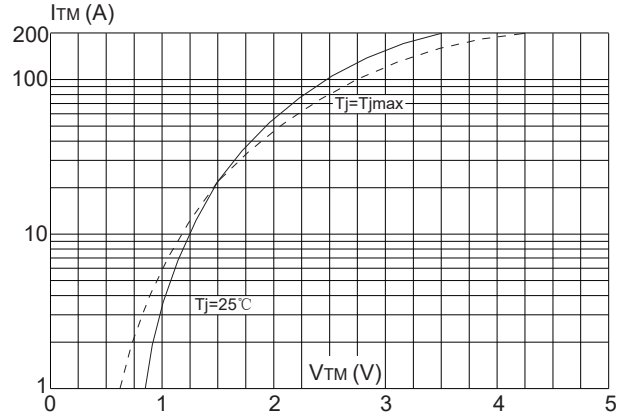


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 50A/\mu s$)

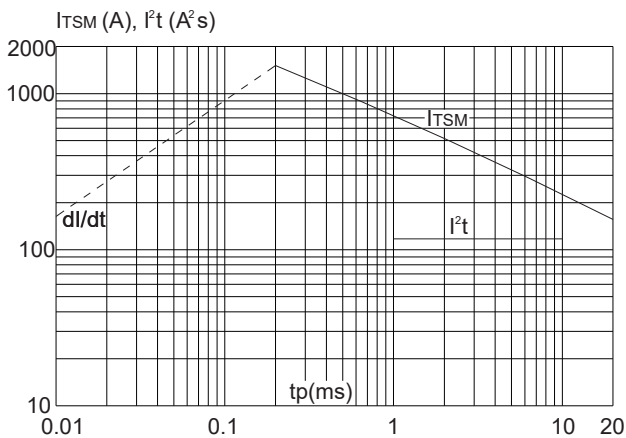
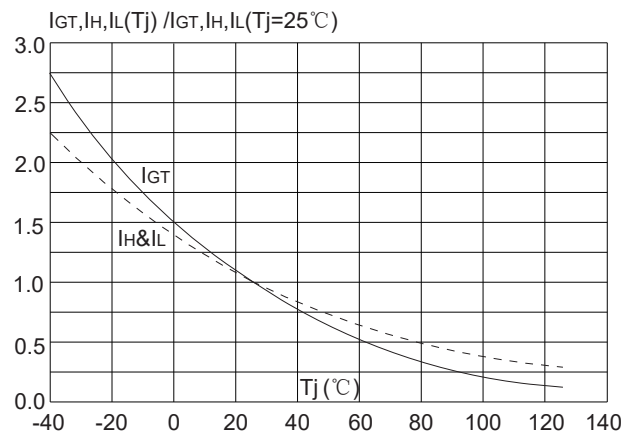


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

